

Supporting Information

Ultra-thin lead oxide piezoelectric layers for reduced environmental contamination using a liquid metal-based process

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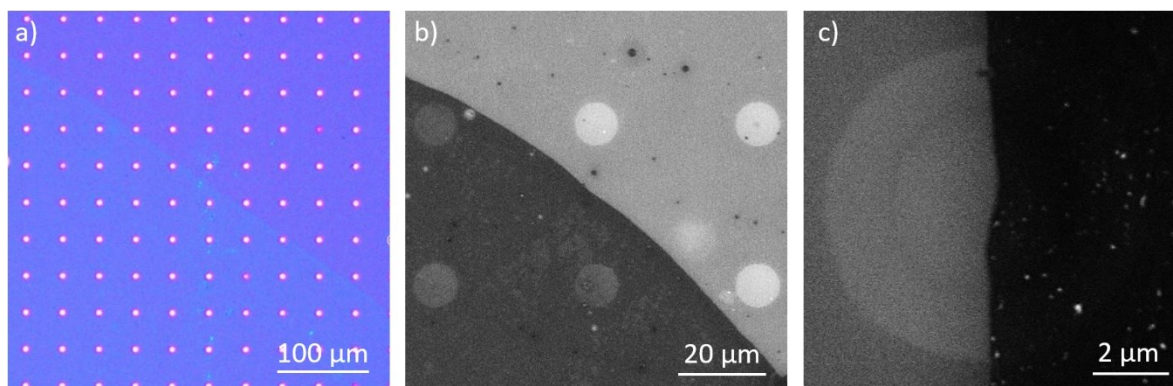


Fig. S1 (a) Optical and (b,c) SEM images of the 2D PbO on a holey SiO₂/Si substrate.

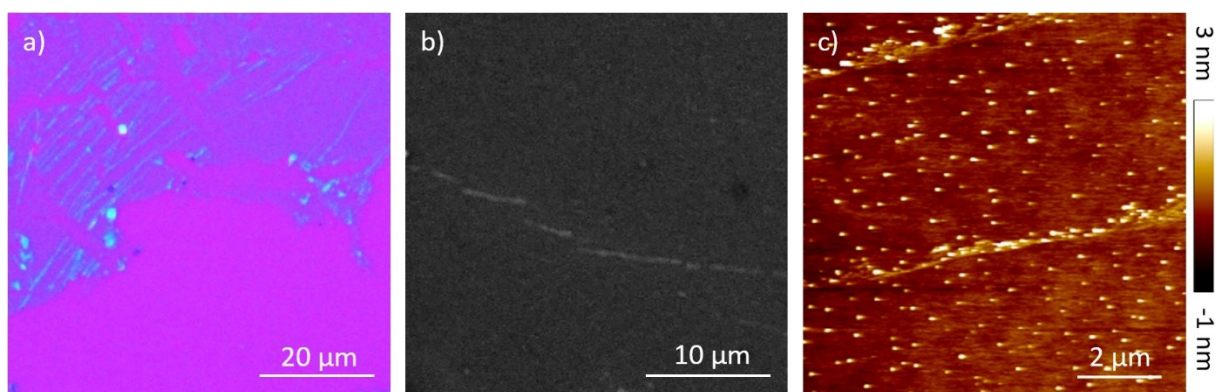


Fig. S2 (a) Optical, (b) SEM and (c) AFM images of the 2D PbO wrinkles on a SiO₂/Si substrate.

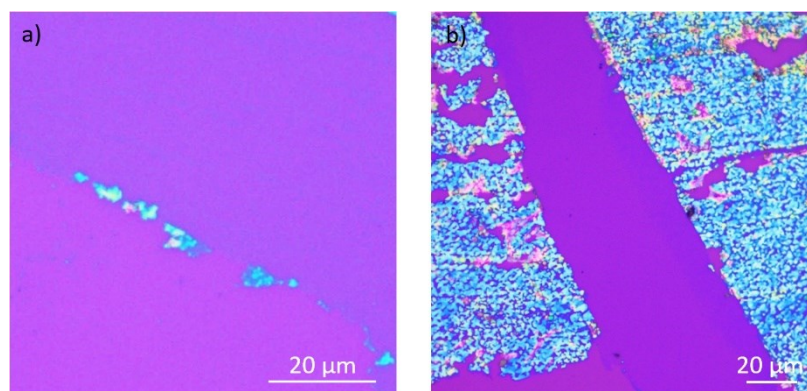


Fig. S3 Bulk lead oxides on the edges of monolayer PbO after (a) short and (b) long (15 min) oxidation periods.

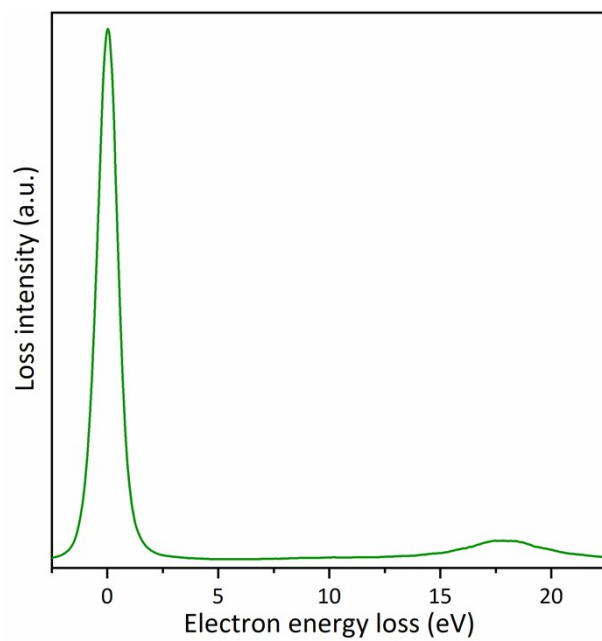


Fig. S4 The EELS spectrum of 2D PbO nanosheets.

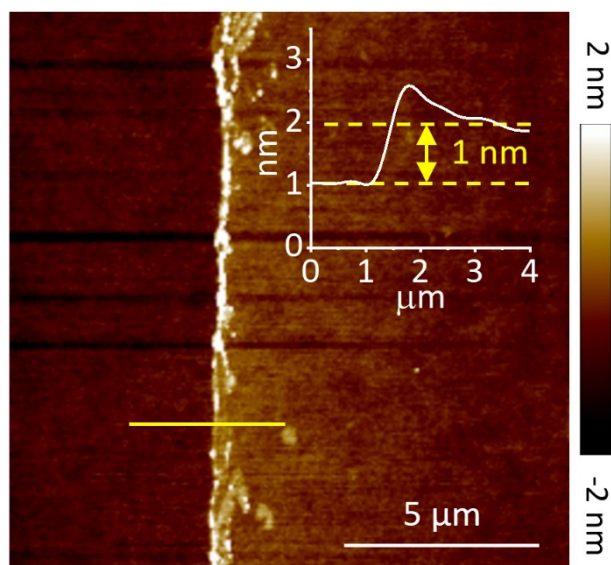


Fig. S5 The AFM image of the area of 2D PbO used for piezoelectricity measurements.



Fig. S6 Topography, amplitude, and phase variation of PPLN as the function of magnitudes of AC driving voltages.

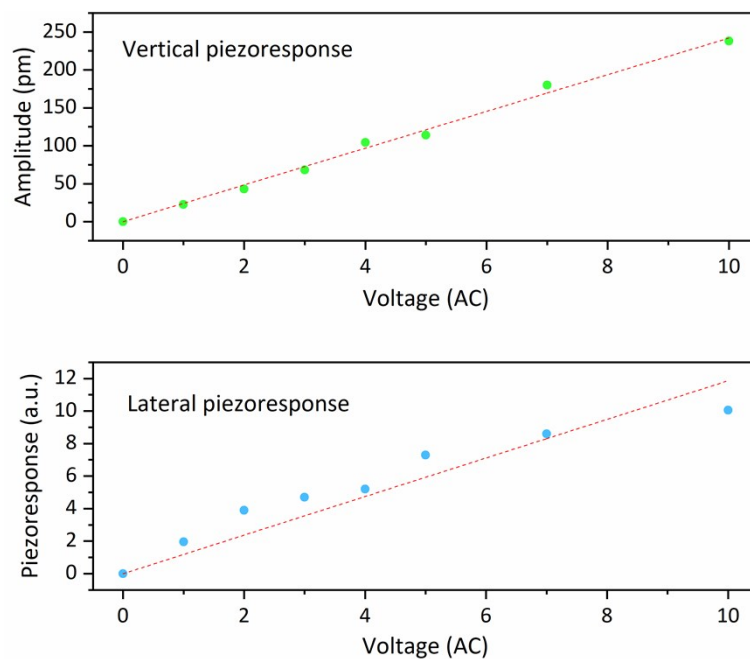


Fig. S7 Extended vertical and lateral piezoresponse amplitudes of the PbO monolayer as the function of AC driving voltage.

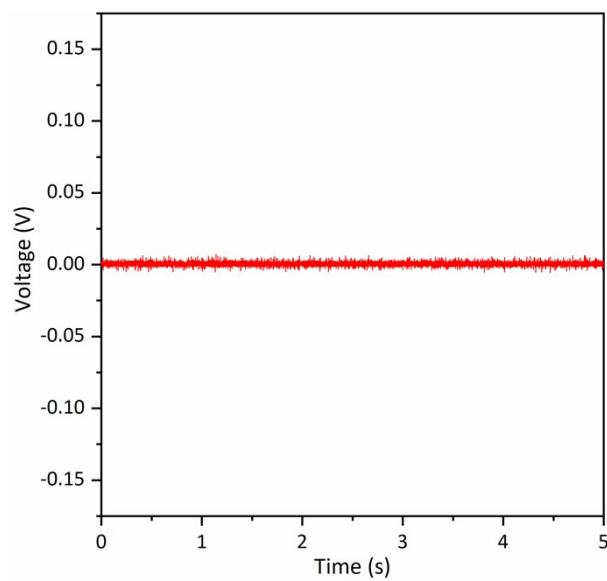


Fig. S8 Voltage output from the bare (no PbO layer) mica device after applying mechanical stimuli.

Table S1. Computed piezoelectric stress tensor (in C m⁻²) and relevant elastic tensors (in GPa) components for a metastable β -PbO structure.

e_{31}	e_{32}	e_{33}	C_{11}	C_{12}	C_{13}	C_{22}	C_{23}	C_{33}
0.069	0.069	-0.173	4.4	0.8	0.8	11.8	3.0	7.4

Table S2. Vertical and lateral piezoresponses of some 2D materials.

Material	Vertical piezoresponse (pm/V)	Lateral piezoresponse (pm/V)	Ref.	Material	Vertical piezoresponse (pm/V)	Lateral piezoresponse (pm/V)	Ref.
C ₃ N ₄	1		1	GaSe	2.30		2
MoSSe		0.020	3	GaS	2.06		2
MoSTe		0.028	3	InSe	1.46		2
MoSeTe		0.030	3	Graphene oxide		0.24	4
WSSe		0.011	3	GaInTe ₂		0.32	5
WSTe		0.007	3	GaInSe ₂		0.46	5
WSeTe		0.008	3	GaInS ₂		0.38	5
MoS ₂	1.35		6	Ga ₂ SeTe		0.21	5
GaPO ₄	8.5		7	Ga ₂ STe		0.25	5
α -In ₂ Se ₃	0.34		8	Ga ₂ SSe		0.07	5
CdS	32.8		9	In ₂ SeTe		0.13	5
ZnO	23.7		10	In ₂ STe		0.25	5
ZnO	21.5		11	In ₂ SSe		0.18	5
Graphene on SiO ₂	14		12	MoS ₂	1.03		13
Graphene doped with K		0.23	14	MoSSe	0.1		15
Graphene doped with Li		0.15	14	BaTiO ₃	8		16
Graphene doped with H		0.11	14	PVDF	-36		17
Graphene doped with F		0.0018	14	PZT	7-15		18
Graphene doped with F, Li		0.30	14	PbO	29.6	3.9	This work
Graphene doped with H, F		0.034	14				

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